TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

TA75W558FU

DUAL OPERATIONAL AMPLIFIER

TA75W558FU is a low-noise monolithic precision operational amplifier.

FEATURES

- Internal Frequency Compensation Type.
- Pin Compatible with TA75W01FU.
- Wide Band Range : $f_T = 3MHz$ (Typ.)
- Noise Voltage Range : $V_{NI} = 2.5 \mu V_{rms}$ (Typ.)
- Power Supply Range : $\pm 4V_{DC}$ to $\pm 18V_{DC}$
- Suitable Application for Active Filter Equalizer Amplifier and Headphone Amplifier.



MARKING (TOP VIEW)



PIN CONNECTION (TOP VIEW)



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EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC} , V _{EE}	± 18	V
Differential Input Voltage	DVIN	± 30	V
Input Voltage	VIN	V _{EE} ~V _{CC}	V
Power Dissipation	PD	250	mW
Operating Temperature	T _{opr}	- 40~85	°C
Storage Temperature	T _{stg}	- 55~125	°C

CHARACTERISTICS	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Offset Voltage	VIO	_	Rg≦10kΩ		0.5	6	mV
Input Offset Current	lio	_	—	_	5	200	nA
Input Bias Current	Ц	—	—	_	60	500	nA
Common Mode Input Voltage	CMV _{IN}	_	—	± 12	± 14	_	v
Maximum Output Voltage	∨ом	_	$R_L = 10k\Omega$	± 12	± 14	_	v
	VOMR	—	$R_L = 2k\Omega$	± 10	±13	—	
Source Current	l _{source}		—	_	40	—	mA
Sink Current	l _{sink}	_	—		40	—	mA
Voltage Gain (Open Loop)	Gv	_	$V_{OUT} = \pm 10V, R_L = 2k\Omega$	86	100	—	dB
Common Mode Input Signal Rejection Ratio	CMRR	_	Rg≤10kΩ	70	90	_	dB
Supply Voltage Rejection Ratio	SVRR		Rg≦10kΩ		30	150	μV/V
Slew Rate	SR	_	$G_V = 1$, $R_L = 2k\Omega$	_	1.0	—	V/μs
Unity Gain Cross Frequency	fT	_	—	_	3.0	—	MHz
Supply Current	Icc	_	—	_	4.0	6.0	mA
Equivalent Input Noise Voltage	V _{NI}	_	$R_s = 1k\Omega$, f = 30Hz~30kHz		2.5	_	μV _{rms}

ELECTRICAL CHARACTERISTICS ($V_{CC} = 15V$, $V_{EE} = -15V$, $Ta = 25^{\circ}C$)



OUTLINE DRAWING SSOP8-P-0.65

Unit : mm





Weight : 0.021g (Typ.)